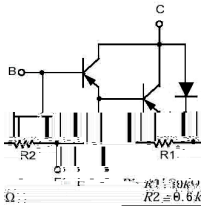
TO-220 PNP Silicon PNP transistor in a TO-220 Plastic Package.

TIP112

Complement to TIP112.

Medium power linear switching applications.

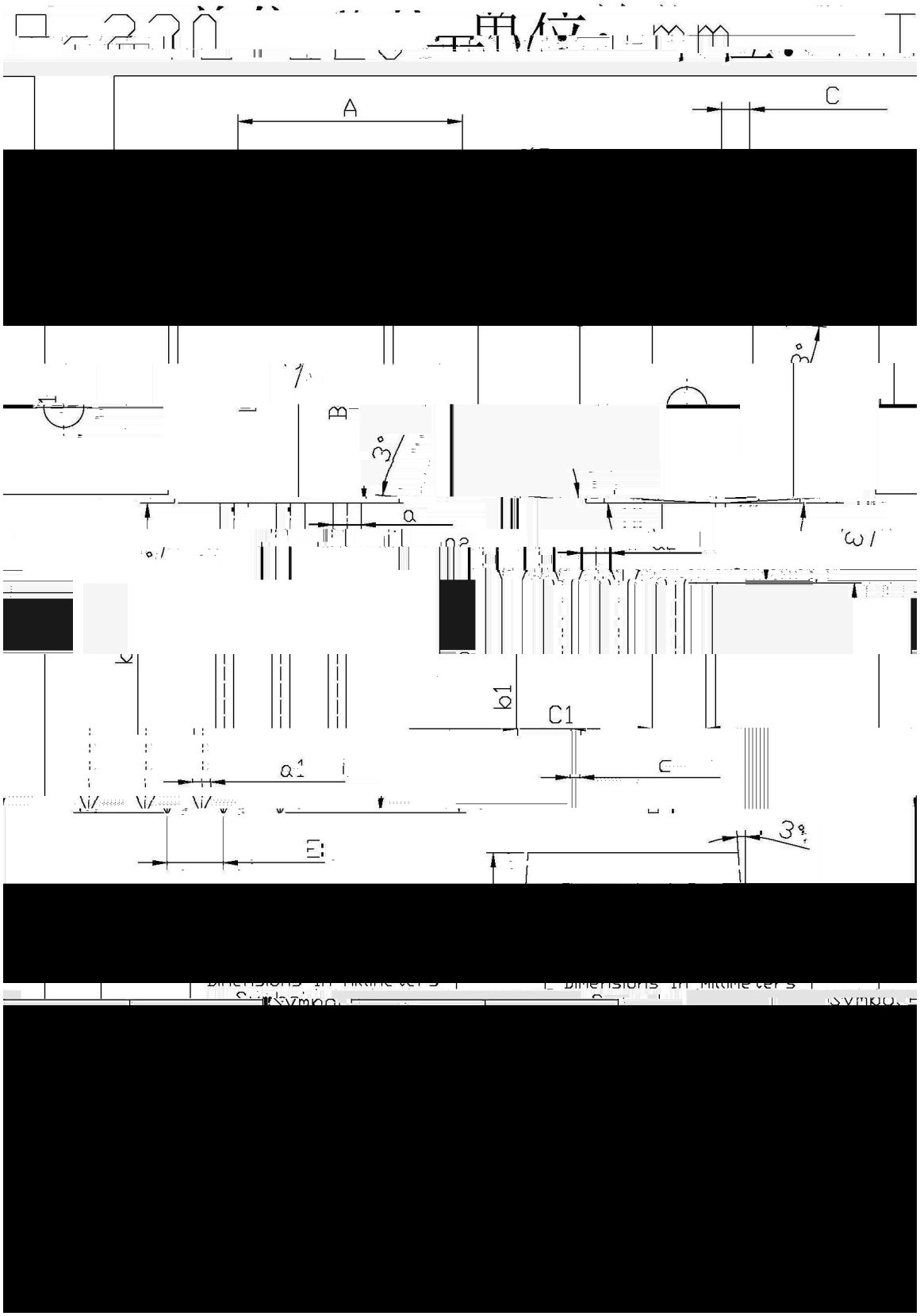


PIN1 Base PIN 2 Collector PIN 3 Emitter

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Peak Collector Current	I_{CP}	-4.0	A
Base Current - Continuous	I_B	-50	mA
Collector Power Dissipation	P_C(Tc=25)	50	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-30mA I_B=0	-100			V
Collector Cut-Off Current	I_{CEO}	V_{CE}=-50V I_B=0			-2.0	mA
Collector Cut-Off Current	I_{CBO}	V_{CB}=-100V I_E=0			-1.0	mA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5V I_C=0			-2.0	mA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-4V I_C=-1A	1000			
	$h_{FE(2)}$	V_{CE}=-4V I_C=-2A	500			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-2A I_B=-8mA			-2.5	V
Base to Emitter On Voltage	$V_{BE(on)}$	I_C=-2A V_{CE}=-4V			-2.8	V
Collector output capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=0.1MHz			200	pF


A
C
B
3°
a
b1
C1
a1
E1
3°